OptiMOS®-P2 Power-Transistor

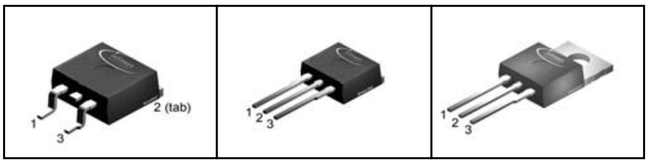
Product Summary

V_{DS}	-30	V
$R_{DS(on)}$ (SMD Version)	6.9	mΩ
I_D	-80	A

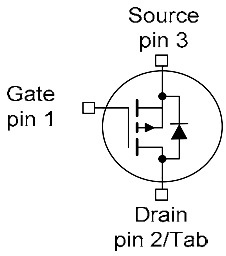
Features

- P-channel - Logic Level - Enhancement mode
- AEC qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green package (RoHS compliant)
- 100% Avalanche tested
- Intended for reverse battery protection

PG-TO263-3-2 PG-TO262-3-1 PG-TO220-3-1



Type	Package	Marking
IPB80P03P4L-07	PG-TO263-3-2	4P03L07
IPI80P03P4L-07	PG-TO262-3-1	4P03L07
IPP80P03P4L-07	PG-TO220-3-1	4P03L07



Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_C=25°C, V_{GS}=-10V[1)	-80	A
		T_C=100°C, V_{GS}=-10V[2)	-65	
Pulsed drain current[2)	$I_{D,pulse}$	T_C=25°C	-320	
Avalanche energy, single pulse	E_{AS}	I_D=-40A	135	mJ
Avalanche current, single pulse	I_{AS}	-	-80	A
Gate source voltage	V_{GS}	-	+5/-16	V
Power dissipation	P_{tot}	T_C=25 °C	88	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics[2]						
Thermal resistance, junction - case	R_{thJC}	-	-	-	1.7	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	-	62	
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm^2 cooling area[3]	-	-	40	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D= -1mA	-30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-130µA	-1.0	-1.5	-2.0	
Zero gate voltage drain current	I_{DSS}	V_{DS}=-24V, V_{GS}=0V, T_j=25°C	-	-0.03	-1	µA
		V_{DS}=-24V, V_{GS}=0V, T_j=125°C[2]	-	-10	-100	
Gate-source leakage current	I_{GSS}	V_{GS}=-16V, V_{DS}=0V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=-4.5V, I_D=-40A	-	8.3	12.3	mΩ
		V_{GS}=-4.5V, I_D=-40A, SMD version	-	8.0	12	
		V_{GS}=-10V, I_D=-80A	-	5.9	7.2	
		V_{GS}=-10V, I_D=-80A, SMD version	-	5.6	6.9	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics[2)]						
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-25V, f=1MHz	-	4400	5700	pF
Output capacitance	C_{oss}		-	1220	1600	
Reverse transfer capacitance	C_{rss}		-	30	60	
Turn-on delay time	$t_{d(on)}$	V_{DD}=-15V, V_{GS}=-10V, I_D=-80A, R_G=3.5Ω	-	8	-	ns
Rise time	t_r		-	4	-	
Turn-off delay time	$t_{d(off)}$		-	15	-	
Fall time	t_f		-	60	-	
Gate Charge Characteristics[2)]						
Gate to source charge	Q_{gs}	V_{DD}=-24V, I_D=-80A, V_{GS}=0 to -10V	-	16	20	nC
Gate to drain charge	Q_{gd}		-	8	16	
Gate charge total	Q_g		-	63	80	
Gate plateau voltage	$V_{plateau}$		-	-3.7	-	V
Reverse Diode						
Diode continous forward current[2)]	I_S	T_C=25°C	-	-	-80	A
Diode pulse current[2)]	$I_{S,pulse}$		-	-	-320	
Diode forward voltage	V_{SD}	V_{GS}=0V, I_F=-80A, T_j=25°C	-	-	-1.3	V
Reverse recovery time[2)]	t_{rr}	V_R=-15V, I_F=-80A, di_F/dt=-100A/µs	-	50	-	ns
Reverse recovery charge[2)]	Q_{rr}		-	40	-	nC

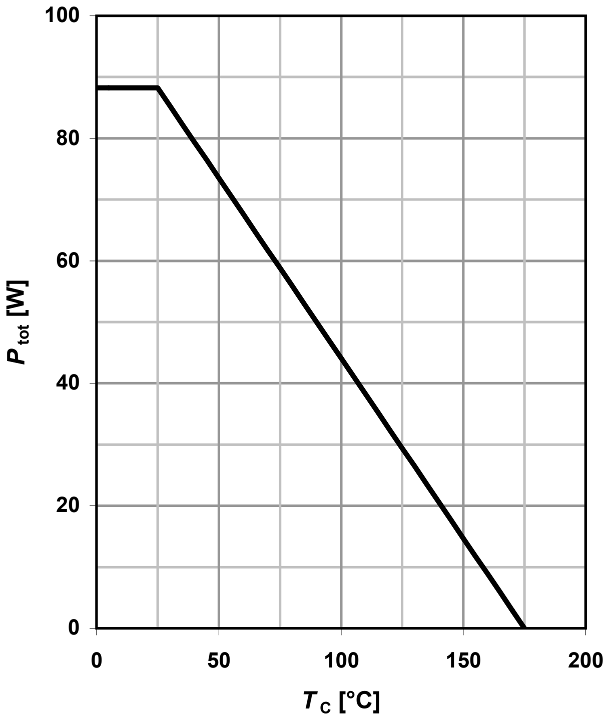
[1)] Current is limited by bondwire; with an R_{thJC} = 1.7K/W the chip is able to carry 92A at 25°C.

[2)] Defined by design. Not subject to production test.

[3)] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

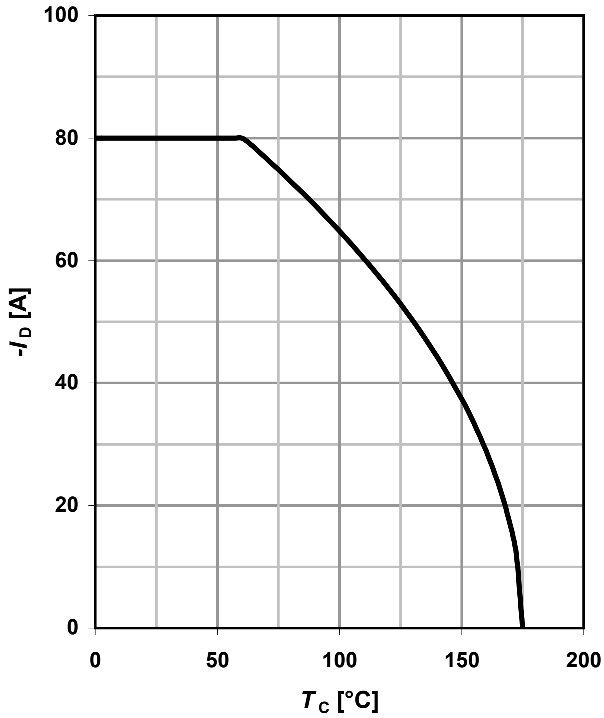
1 Power dissipation

$P_{tot} = f(T_C)$; $V_{GS} \leq -6V$



2 Drain current

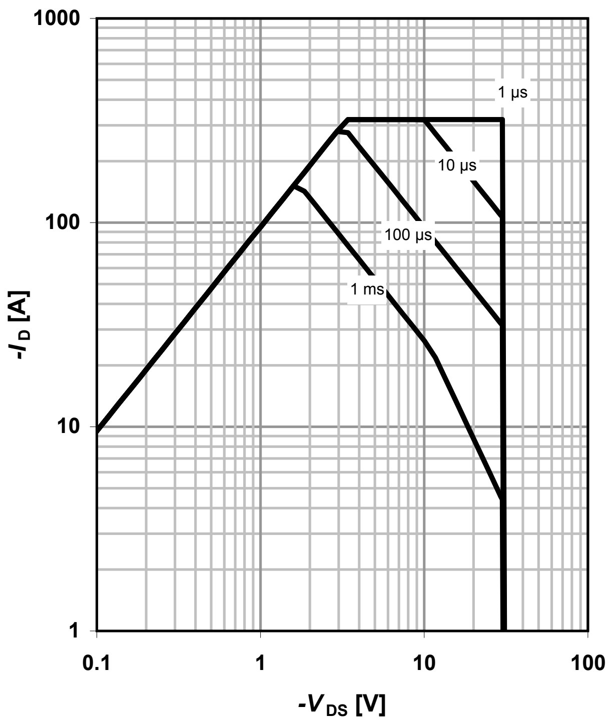
$I_D = f(T_C)$; $V_{GS} \leq -6V$; SMD



3 Safe operating area

$I_D = f(V_{DS})$; $T_C = 25$ °C; $D = 0$; SMD

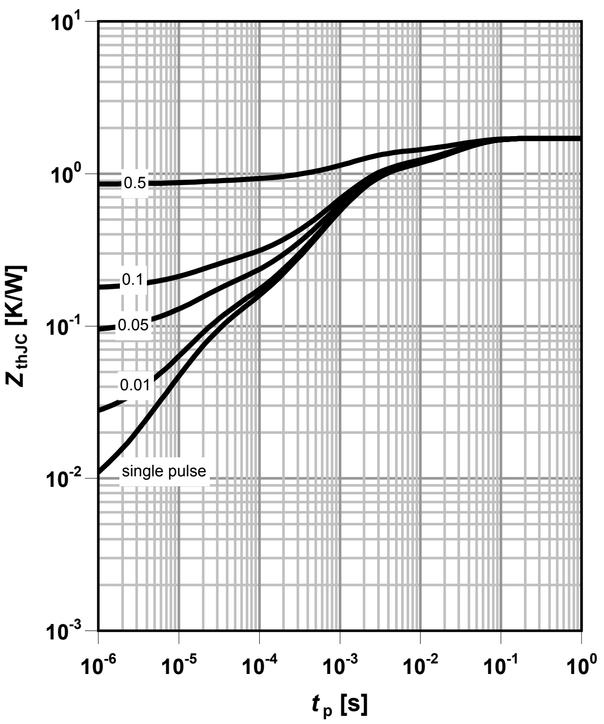
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

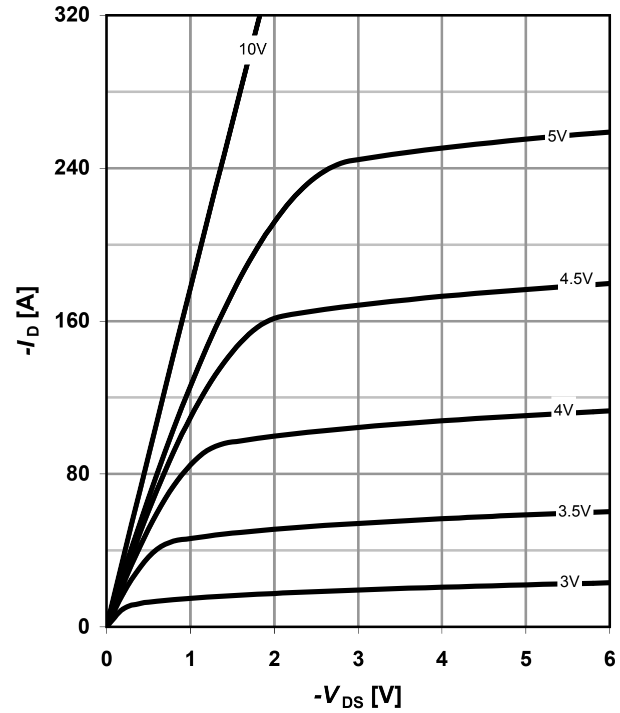
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS})$; $T_j = 25$ °C; SMD

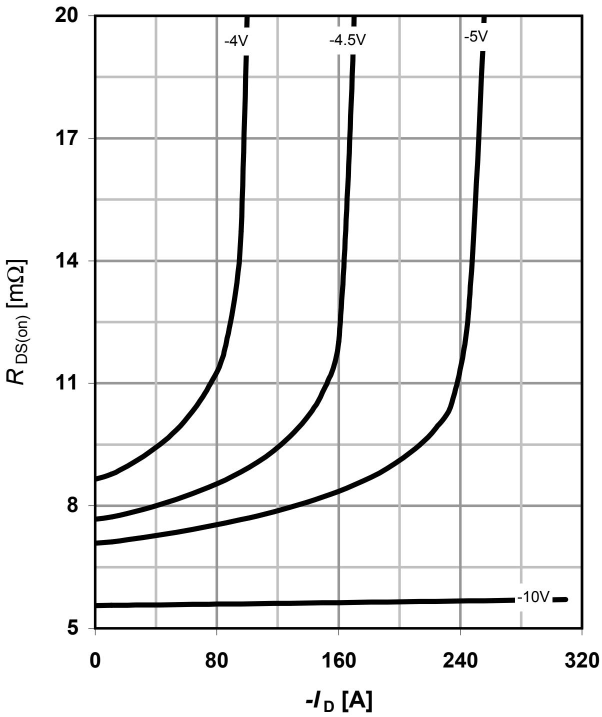
parameter: V_{GS}



6 Typ. drain-source on-state resistance

$R_{DS(on)} = (I_D)$; $T_j = 25$ °C; SMD

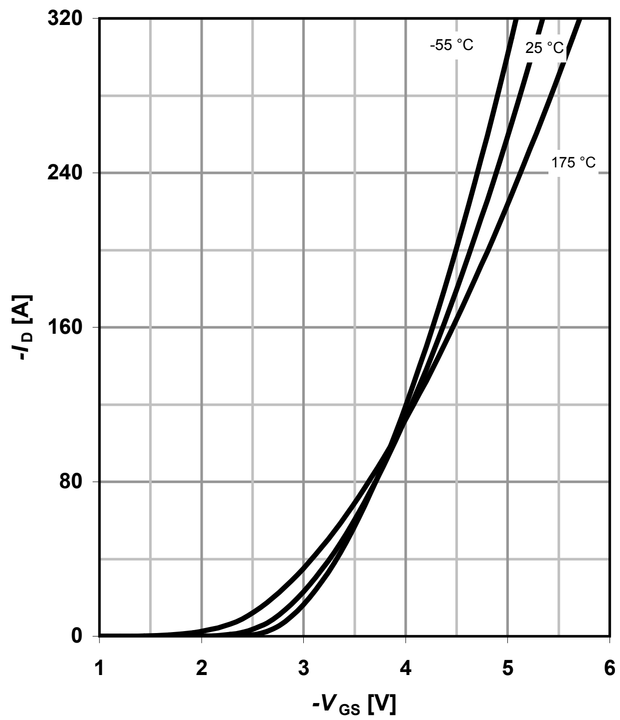
parameter: V_{GS}



7 Typ. transfer characteristics

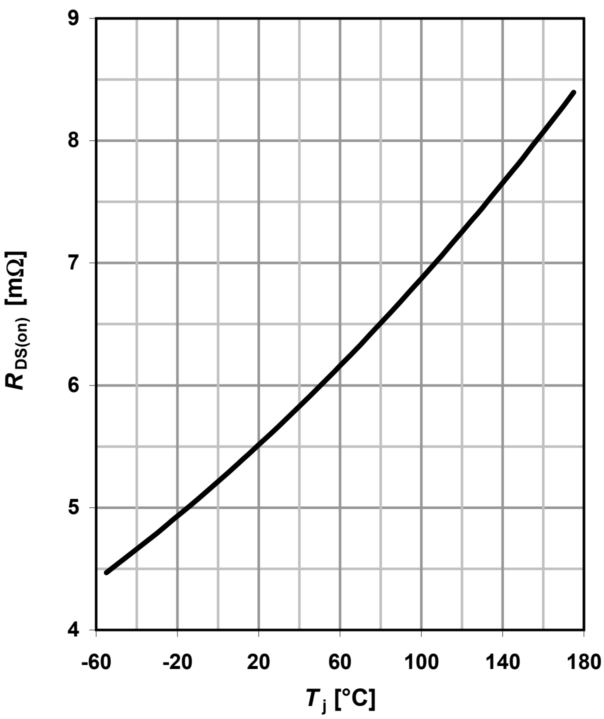
$I_D = f(V_{GS})$; $V_{DS} = -6$V

parameter: T_j



8 Typ. drain-source on-state resistance

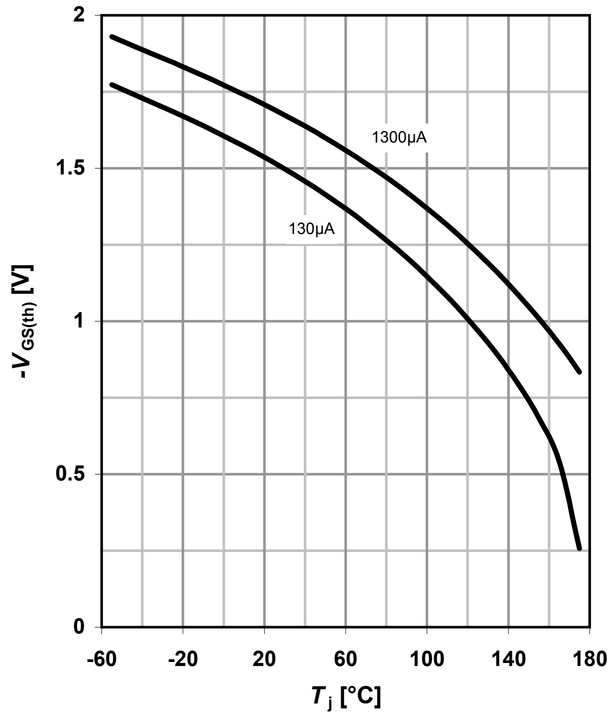
$R_{DS(on)} = f(T_j)$; $I_D = -80$ A; $V_{GS} = -10$ V; SMD



9 Typ. gate threshold voltage

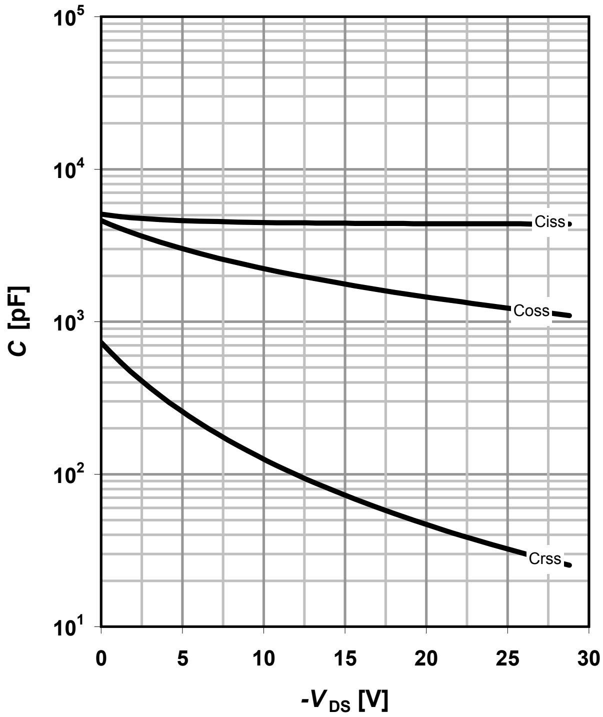
$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$

parameter: $-I_D$



10 Typ. capacitances

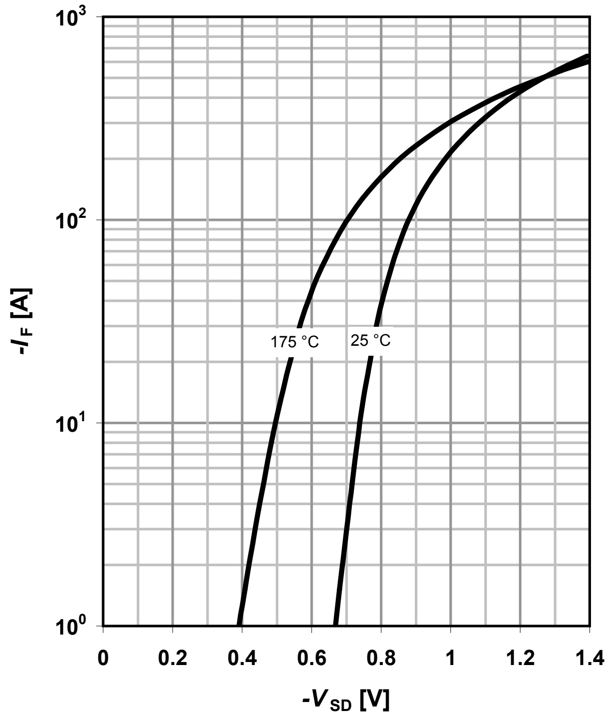
$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz



11 Typical forward diode characteristicis

IF = $f(V_{SD})$

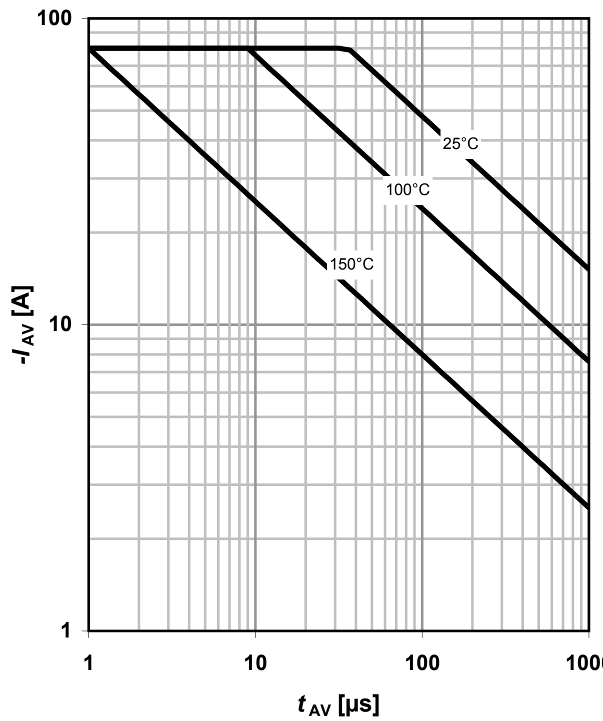
parameter: T_j



12 Avalanche characteristics

$I_{AS} = f(t_{AV})$

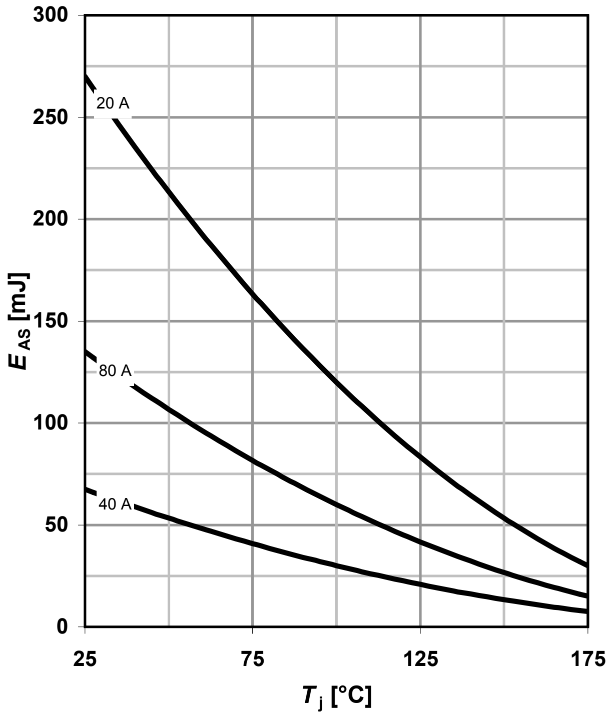
parameter: $T_{j(start)}$



13 Avalanche energy

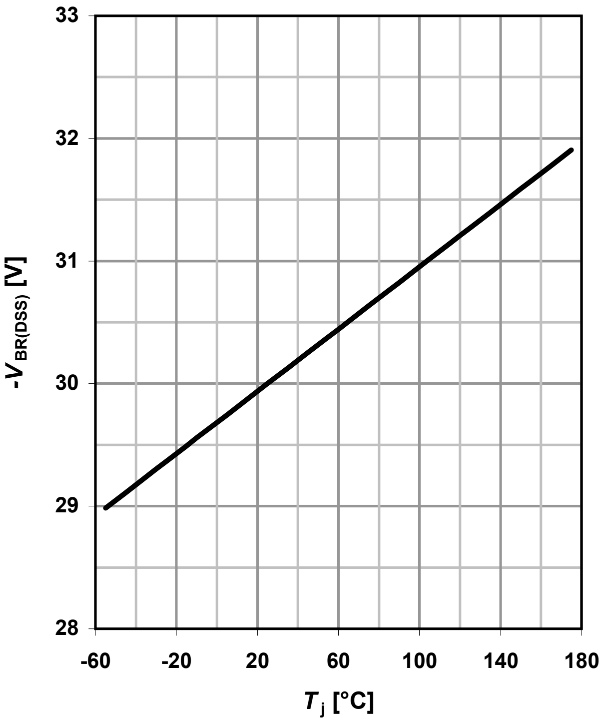
$E_{AS} = f(T_j)$

parameter: I_D



14 Drain-source breakdown voltage

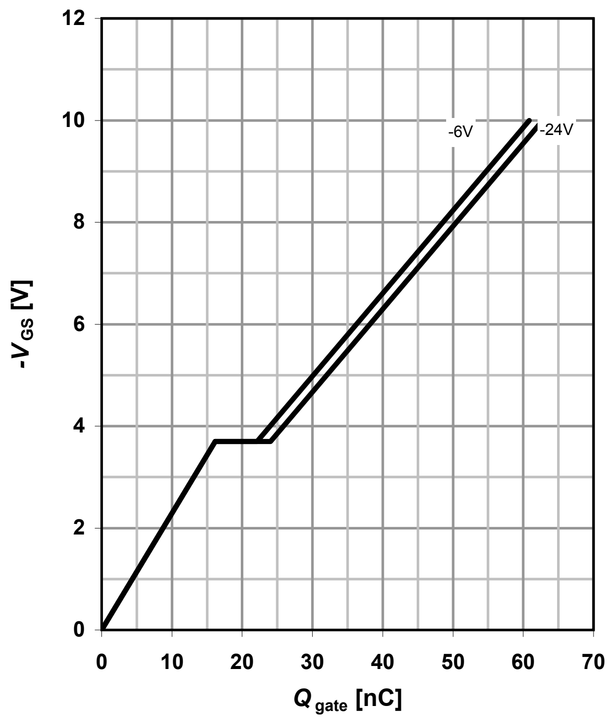
$V_{BR(DSS)} = f(T_j)$; $I_D = -1$ mA



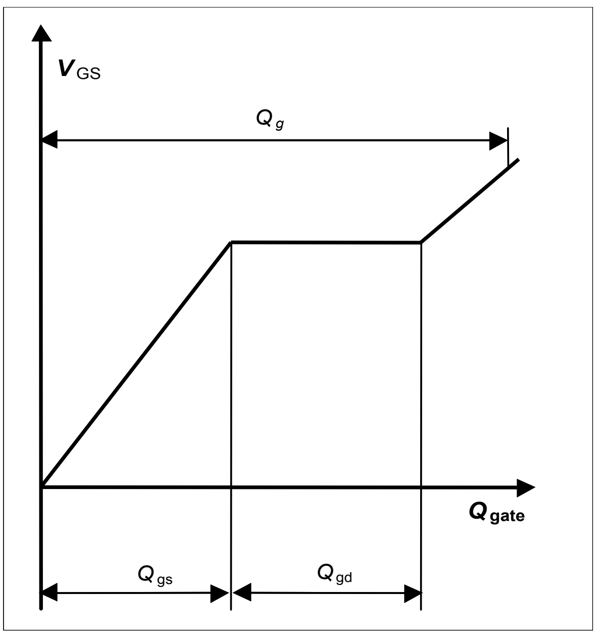
15 Typ. gate charge

$V_{GS} = f(Q_{gate})$; $I_D = -80$ A pulsed

parameter: V_{DD}



16 Gate charge waveforms



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Revision History

Version	Date	Changes

Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

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